IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Theodore W. Houston

Serial No.:

N/A

Filed:

Herewith

For:

A MULTI-GATE ONE-TRANSISTOR DYNAMIC RANDOM

ACCESS MEMORY

Group No.:

N/A

Examiner:

N/A

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

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LOUZA DELT

Sir:

INFORMATION DISCLOSURE STATEMENT

Pursuant to the duty of disclosure under 37 C.F.R. § 1.56, Applicant submits this statement. This submittal is made in accordance with 37 C.F.R. §§ 1.97 and 1.98 and § 609 of the Manual of Patent Examining Procedure. The patents, publications and other information herein are listed below and on the attached Form PTO-1449. Copies of the listed references are submitted herewith.

U.S. Patent No.	Inventor	<u>Date</u>
6,396,108 B1 6,307,230 B1 6,225,175 B1	Krivokapic et al. Chatterjee et al. Houston	May 28, 2002 October 23, 2001 May 1, 2001
Foreign Patent No.	Country	<u>Date</u>
WO 02/103703 A2	WO	December 27, 2002

References:

Kazumi Inoh, Tomoaki SHino, Hiroaki Yamada, Hiroomi Nakajima, Yoshihiro Minami, Takashi Yamada, Takashi Ohsawa, Tomoki Higashi, Katsuyuki Fujita, Tamio Ikehashi, Takeshi Kajiyama, Yoshiaki Fukuzumi, Takeshi Hamamoto and Hidemi Ishiuchi;"FBC (FLOATING BODY CELL) FOR EMBEDDED DRAM ON SOI"; 2003 Symposium on VLSI Technology Digest of Technical Papers; pgs 1-2.

Takashi Ohsawa, Tomoki Higashi, Katsuyuki Fujita, Tamio Ikehashi, Takeshi Kajiyama, Yoshiaki Fukuzumi, Tomoaki Shino, Hiroaki Yamada, Hiroomi Nakajima, Yoshihiro Minami, takashi Yamada, Kazumi Inoh, Takeshi Hamamoto; "A MEMORY USING ONE-TRANSISTOR GAIN CELL ON SOI (FBC) WITH PERFORMANCE SUITABLE FOR EMBEDDED DRAM'S"; 2003 Symposium on VLSI Circuits Digest of Technical Papers; Pgs1-4.

B. Doyle, B. BOyanov, S. Datta, M. Doczy, S. Harland, B. Jin J. Kavalieros, T. Linton, R. Rios & R. Chau; "TRI-GATE FULLY-DEPLETED CMOS TRANSISTORS: FABRICATION, DESIGN AND LAYOUT"; 2003 Symposium on VLSI Technology Digest of Technical Papers; Pgs.1-2.

Applicant hereby expressly reserves the right to swear behind the effective dates of any of the above Patents and to question the relevance and materiality of the Patents and Publications listed herein, in whole, in part, or in combination, subsequent to filing this Information Disclosure Statement. The Commissioner is hereby authorized to charge any fees which may be required, or

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Respectfully submitted,

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Substitute for form 1449/PTO				Complete if Known			
				Application Number	N/A		
INFORMATION DISCLOSURE				Filing Date	Herewith		
				First Named Inventor	Theodore Houston, et al.		
STATEMENT BY APPLICANT				Art Unit	N/A	-	
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eet	1	of	2	Attorney Docket Number	TI 35657		

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Examiner	Cite	Dogumant Numb -:		DOCUMENTS	
Initials*	Cite No. ¹	Document Number Number-Kind Code ^{2 (f known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US- 6,396,108 B1	05/28/ 2002	Krivokapic et al.	
		⁰⁵⁻ 6,307,230 B1	10/23/2001	Chatterjee et al.	
		^{US-} 6,225,175 B1	05/01/2001	Houston	
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		FORE	IGN PATENT DOCU	IMENTS		
Examiner Initials*	Cite No.1	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages	Π
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)	MM-DD-YYYY	Private of Chou Doubling	Or Relevant Figures Appear	T ⁶
		WO 02/103703 A2	12/27/2002	Innovative Silicon SA		
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This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

PTO/SB/08B (08-03)

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INFO	ORMATIO	N DIS	CLOSURE	Filing Date	Herewith	
STATEMENT BY APPLICANT			PPLICANT	First Named Inventor	Theodore Houston, et al.	
(Use as many sheets as necessary)			acoccand	Art Unit	N/A	
			ecessary)	Examiner Name	N/A	
Sheet	2	of	2	Attorney Docket Number	TI 35657	

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Kazumi Inoh, Tomoaki SHino, Hiroaki Yamada, Hiroomi Nakajima, Yoshihiro Minami, Takashi Yamada, Takashi Ohsawa, Tomoki Higashi, Katsuyuki Fujita, Tamio Ikehashi, Takeshi Kajiyama, Yoshiaki Fukuzumi, Takeshi Hamamoto and Hidemi Ishiuchi;"FBC (FLOATING BODY CELL) FOR EMBEDDED DRAM ON SOI"; 2003 Symposium on VLSI Technology Digest of Technical Papers; pgs 1-2.	
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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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